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number. Substitute for form 1449B/PTOR MADENAS

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

Date Submitted: 1/7/05

(use as many sheets as necessary) 1 of 7 Sheet

Application Number	10/784,586	
Filing Date	02/23/2004	
First Named Inventor	Harry A. ATWATER et al.	
Group Art Unit	1764	
Examiner Name	Unassigned	
Attorney Docket Number	047071-0109	

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Examiner Cite No.1	Cit-	U.S. Patent (Document	Name of Both of a second of	Date of Publication of	Pages, Columns, Lines, Where Relevant			
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Examiner Signature	/Shamim Ahmed/ (08/20/2006)	Date Considered	08/20/2006

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¹ Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-latter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁴Kind of document by the appropriate symbols as Indicated on the document under WIPO Standard ST. 16 if possible. ⁴Applicant is to place a check mark here if English language Translation is attached.

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	Substitute fo	or form 1449B	/PTO	Complete if Known			
	INFORMATI	ON DISCLO	SURE	Application Number	10/784,586		
STATEMENT BY APPLICANT				Filing Date	02/23/2004		
	Data Su	bmitted: 1/7/	/O.S.	First Named Inventor	Harry A. ATWATER et al.		
	Date Su	omitted. 1777	105	Group Art Unit	1764		
	(use as many :	sheets as ne	ecessary)	Examiner Name	Unassigned		
Sheet	2	of	7	Attorney Docket Number	047071-0109		

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	STATEMEN	T BY APPL	ICANT	Filing Date	02/23/2004		
	Data Sul	omitted: 1/7/	/OE	First Named Inventor	Harry A. ATWATER et al.		
	Date Su	omilieu: 1771	103	Group Art Unit	1764		
	(use as many s	sheets as ne	ecessary)	Examiner Name	Unassigned		
Sheet	3	of	7	Attorney Docket Number	047071-0109		

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	Cite No. ¹	Number	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Cited Document MM-DD-YYYY	Where Relevant Passages or Relevant Figures Appear

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	Substitute for	r form 1449B	/PTO	Complete if Known			
	INFORMATIO	ON DISCLO	SURE	Application Number	10/784,586		
	STATEMENT	BY APPLI	CANT	Filing Date	02/23/2004		
	Data Cub		O.E	First Named Inventor	Harry A. ATWATER et al.		
	Date Sub	mitted: 1/7/	05	Group Art Unit	1764		
	(use as many s	heets as ne	cessary)	Examiner Name	Unassigned		
Sheet	4	of	7	Attorney Docket Number	047071-0109		

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No.1	Number	Kind Code ² (if known)			
	Cite No.1	Cite	No.1 Number Code ² (If	Cite Number Kind Name of Patentee or Applicant of Cited Document	Cite No.1 Number Code ² (if Name of Patentee or Applicant of Cited Document MM-DD-YYYY

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Examiner Initials*	Cite No.1	For Office ³	eign Patent D Number ⁴	ocument Kind Code ⁵ (if known)	Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
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Examiner Initials*		Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T⁵
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number. Substitute for form 1449B/PTO Complete if Known Application Number 10/784,586 INFORMATION DISCLOSURE STATEMENT BY APPLICANT 02/23/2004 Filing Date Harry A. ATWATER et al. First Named Inventor Date Submitted: 1/7/05 **Group Art Unit** 1764 (use as many sheets as necessary) **Examiner Name** Unassigned Sheet 5 of | 7 **Attorney Docket Number** 047071-0109

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	INFORMATION	ON DISCLO	OSURE	Application Number	10/784,586	F 000F
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				First Named Inventor	Harry A. ATWATE	Retal.
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Date Considered Examiner Signature /Shamim Ahmed/ (08/20/2006) 08/20/2006

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STATEMENT BY APPLICANT

Date Submitted: 7/24/06

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Application Number	10/784,586			
Filing Date	2/23/2004			
First Named Inventor	Harry A. Jr. ATWATER			
Group Art Unit	1765			
Examiner Name	S. Ahmed			
Attorney Docket Number	047071-0109			

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